EMZ2 / UMZ2N / IMZ2A

Power management (dual transistors)

Datasheet

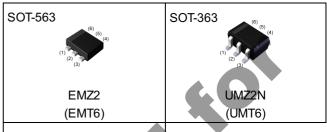
<For Tr1(PNP)>

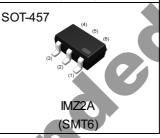
Parameter	Value
V _{CEO}	-50V
I _C	-150mA

<For Tr2(NPN)>

Parameter	Value		
V _{CEO}	50V		
I _C	150mA		

Outline





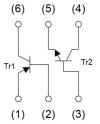
Features

- 1) Included a 2SA1037AK and a 2SC2412K transistor in a EMT, UMT or SMT package.
- 2)Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3)Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

•Inner circuit

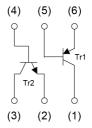
EMZ2 / ÚMZ2N

- (1) Tr1(PNP) Emitter
- (2) Tr1(PNP) Base
- (3) Tr2(NPN) Base
- (4) Tr2(NPN) Collector
- (5) Tr2(NPN) Emitter
- (6) Tr1(PNP) Collector



IMZ2A

- (1) Tr1(PNP) Collector
- (2) Tr2(NPN) Emitter
- (3) Tr2(NPN) Collector
- (4) Tr2(NPN) Base
- (5) Tr1(PNP) Base
- (6) Tr1(PNP) Emitter



Application

GENERAL PURPOSE SMALL SIGNAL AMPLIFIER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
EMZ2	SOT-563 (EMT6)	1616	T2R	180	8	8000	Z2
UMZ2N	SOT-363 (UMT6)	2021	TR	180	8	3000	Z2
IMZ2A	SOT-457 (SMT6)	2928	T108	180	8	3000	Z2

● Absolute maximum ratings (T_a = 25°C)

Parameter			Tr1(PNP)	Tr2(NPN)	Unit
Collector-base voltage			-60	60	V
Collector-emitter voltage			-50	50	V
Emitter-base voltage			-6	7	V
Collector current			-150	150	mA
Dower discinction	EMZ2/ UMZ2N	P _D *1*2	150		mW/Total
Power dissipation	IMZ2A	P _D *1*3	300		mW/Total
Junction temperature			150		°C
Range of storage temperature			-55 to	+150	°C

● Electrical characteristics (T_a = 25°C) <For Tr1(PNP)>

, u	,	l ,		Values		
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector-base breakdown voltage	BV_CBO	I _C = -50μA	-60	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-50		-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = -50μA	-6		-	V
Collector cut-off current	I _{CBO}	V _{CB} = -60V		-	-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -6V		-	-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 \text{mA}, I_B = -5 \text{mA}$		-	-500	mV
DC current gain	h _{FE}	$V_{CE} = -6V, I_{C} = -1mA$	120	-	560	-
Transition frequency	fτ	$V_{CE} = -12V$, $I_{E} = 2mA$, $f = 100MHz$	-	140	-	MHz
Output capacitance	C _{ob}	$V_{CB} = -12V$, $I_E = 2mA$, $f = 100MHz$	-	4.0	5.0	pF

• Electrical characteristics (T_a = 25°C) <For Tr2(NPN)>

Doromator	Parameter Symbol Conditions -		Values			Unit
Falanetei			Min.	Тур.	Max.	Offic
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	60	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	1	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 50μA	7	-	ı	V
Collector cut-off current	I _{CBO}	V _{CB} = 60V	1	-	100	nΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 7V	1	-	100	nΑ
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 50$ mA, $I_B = 5$ mA	1	-	400	V
DC current gain	h _{FE}	V_{CE} = 6V, I_{C} = 1mA	120	-	560	-
Transition frequency	f _T	$V_{CE} = 12V, I_{E} = -2mA,$ f = 100MHz	-	180	-	MHz
Output capacitance	C _{ob}	$V_{CB} = 12V$, $I_E = 0A$, $f = 1MHz$	-	2.0	3.5	pF

^{*1} Each terminal mounted on a reference land.

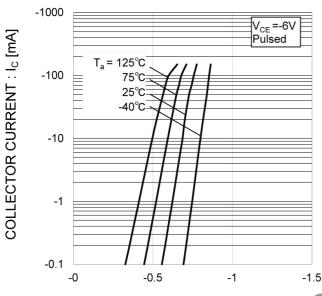


^{*2 120}mW per element must not be exceeded.

^{*3 200}mW per element must not be exceeded.

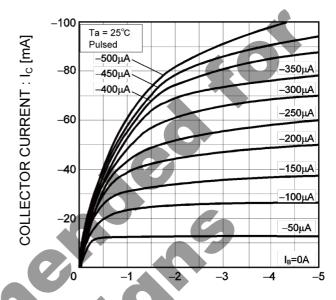
● Electrical characteristic curves(T_a=25°C) <For Tr1(PNP)>

Fig.1 Ground Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE: VBE [V]

Fig.2 Grounded Emitter Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: Vce [V]

Fig.3 DC Current Gain vs. Collector Current (I)

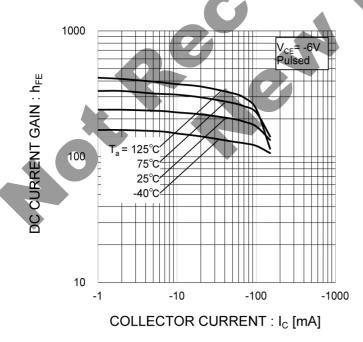
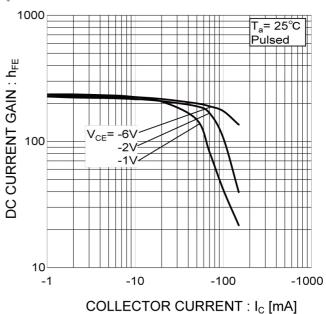


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves(T_a=25°C) <For Tr1(PNP)>

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current(I)

COLLECTOR CURRENT : I_C [mA]

Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (I)

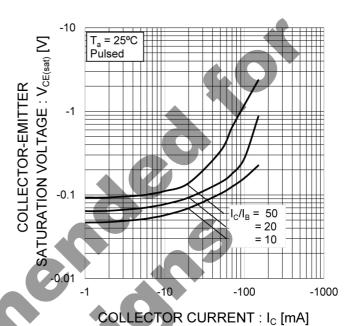


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current (I)

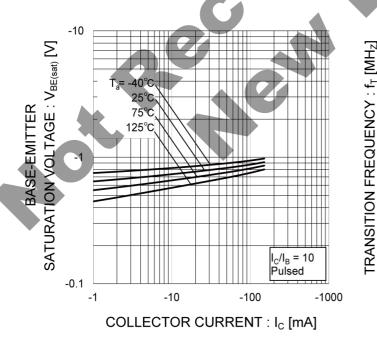
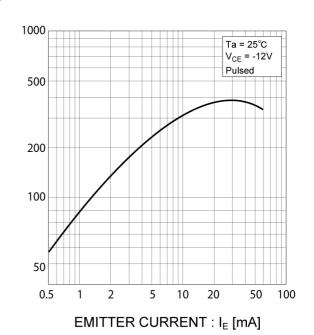


Fig.8 Gain Bandwith Product vs.
Emitter Current



● Electrical characteristic curves(T_a=25°C) < For Tr1(PNP)>

Fig.9 Collector Output Capacitance vs.
Collector-Base Voltage
Emitter Input Capacitance vs.
Emitter-Base Voltage

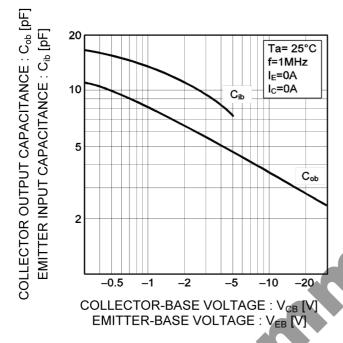


Fig.10 Safe Operating Area

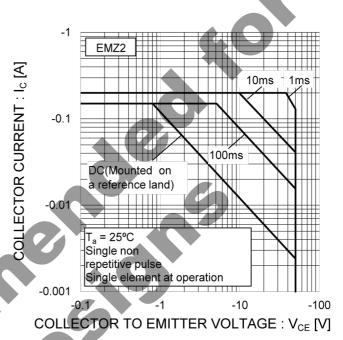


Fig.11 Safe Operating Area

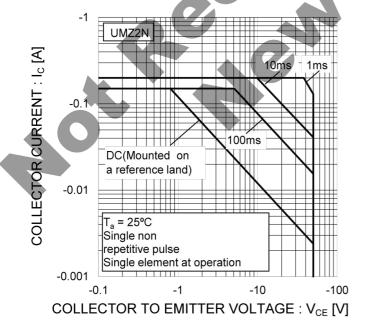
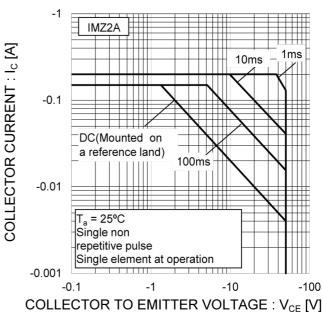


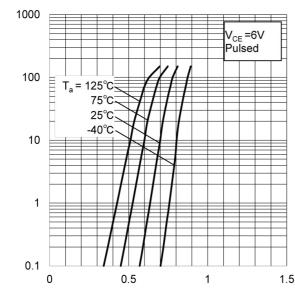
Fig.12 Safe Operating Area



COLLECTOR CURRENT : Ic [mA]

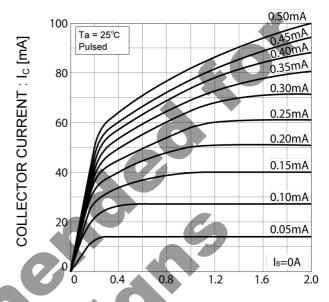
● Electrical characteristic curves(T_a=25°C) <For Tr2(NPN)>

Fig.13 Ground Emitter Propagation Characteristics



BASE TO EMITTER VOLTAGE: VBE [V]

Fig.14 Grounded Emitter Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Fig.15 DC Current Gain vs. Collector Current (I)

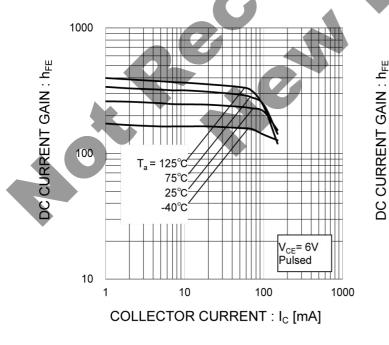
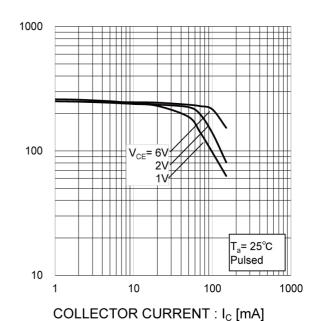


Fig.16 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves (T_a = 25°C) <For Tr2(NPN)>

Fig.17 Collector-Emitter Saturation Voltage vs. Collector Current(I)

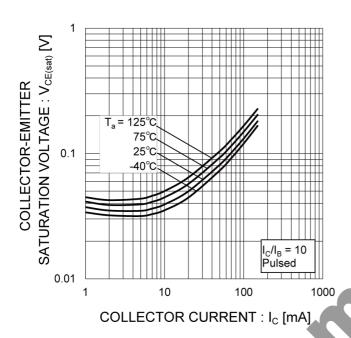


Fig.18 Collector-Emitter Saturation Voltage vs. Collector Current (I)

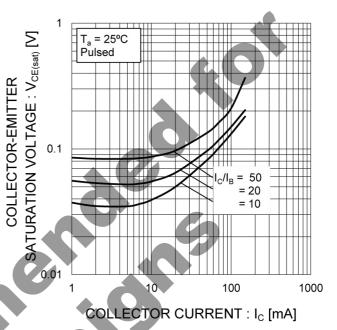


Fig.19 Base-Emitter Saturation Voltage vs. Collector Current (I)

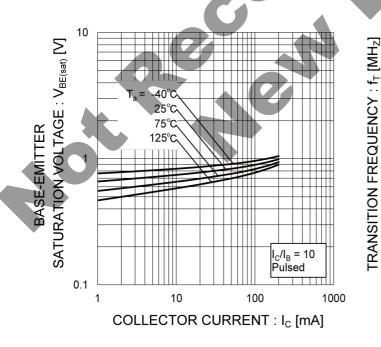
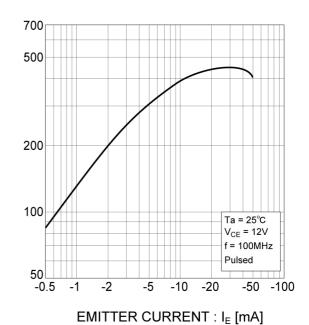


Fig.20 Gain Bandwith Product vs. Emitter Current



● Electrical characteristic curves(T_a = 25°C) < For TR2(NPN)>

Fig.21 Collector Output Capacitance vs.
Collector-Base Voltage
Emitter Input Capacitance vs.
Emitter-Base Voltage

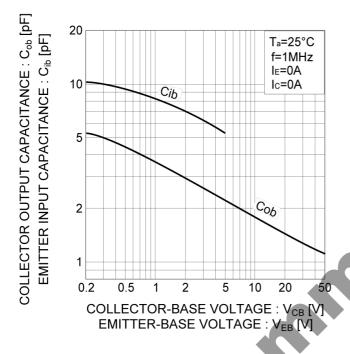


Fig.22 Safe Operating Area

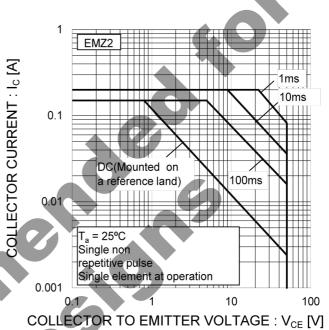


Fig.23 Safe Operating Area

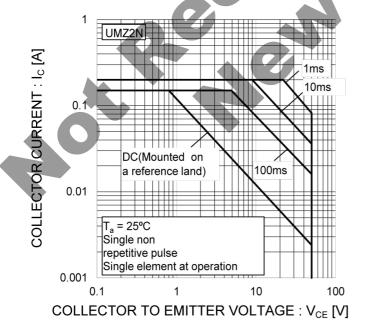
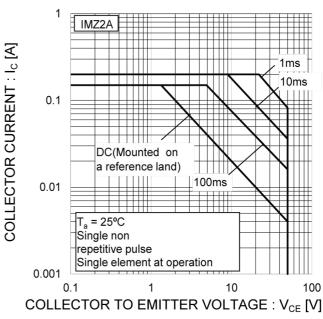
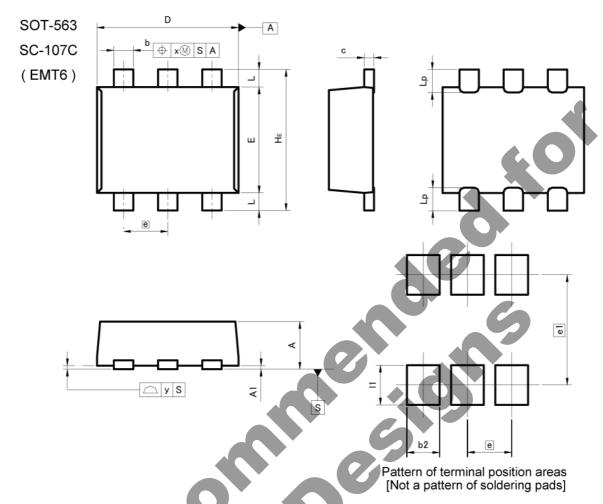


Fig.24 Safe Operating Area



Dimensions

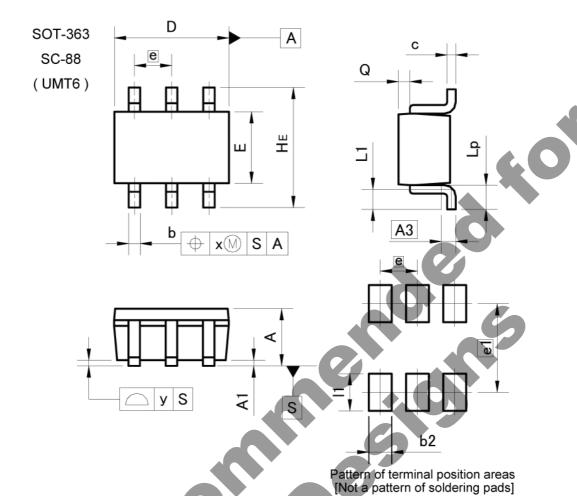


DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
C	0.08	0.18	0.003	0.007
D	1.50	1.70	0.059	0.067
E	1.10	1.30	0.043	0.051
е	0.	50	0.020	
HE	1.50	1.70	0.059	0.067
L	0.10	0.30	0.004	0.012
Lp	1	0.35	-	0.014
×	_	0.10	12	0.004
У	_	0.10	-	0.004

DIM	MILIMETERS		INCHES			
DIM	MIN	MAX	MIN	MAX		
b2	-	0.37	-	0.015		
e1	1.25		0.0	49		
- 11	-	0.45	-	0.018		

Dimension in mm/inches

Dimensions

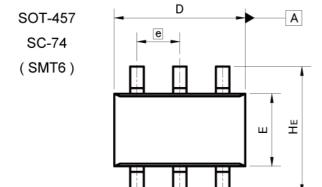


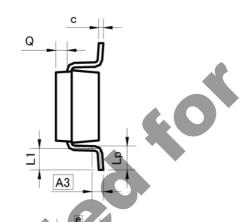
DIM	DIM		INC	HES
DIW	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
(A1	0.00	0.10	0.000	0.004
A3	0.3	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.	65	0.026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
х	-	0.10	s -7	0.004
У		0.10	○ 	0.004

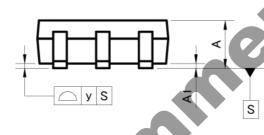
DIM MILIMET		ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
b2	- 7	0.40	-	0.016
e1	1.5	55	0.0	61
11	-	0.65	-	0.026

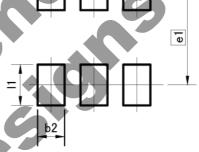
Dimension in mm/inches

Dimensions









Pattern of terminal position areas [Not a pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
DIVI	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.:	25	0.0	10
b	0.25	0.40	0.010	0.016
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.9	95	0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
х		0.20	ī	0.008
У	-	0.10	-	0.004

MILIMETER		MILIMETERS INC		UEC
DIM	IVIILLIVI	MILLIMETERS		
	MIN	MAX	MIN	MAX
b2		0.60	-	0.024
e1	2.	10	0.083	
11	- 2	0.90	-	0.035

Dimension in mm/inches

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